Contributors

Robert L. Bailey (M'63) was born in Spokane, Wash., in 1936. He received the B.S. degree in electrical engineering from Washington State University, Pullman, in 1958, and the M.S. degree in physics from Franklin and Marshall College, Lancaster, Pa., in 1968.

He joined RCA, Lancaster, Pa., in 1958, where he was engaged in the development of UHF circuits for RCA's Cermolox power tubes. From 1961 to 1963, he worked on the design and development of a broad-band S-band power amplifier, and from 1963 to 1965 he was responsible for the design of an L-band broad-band amplifier module developed for the U. S. Army Electronics Laboratory. Since 1965, Mr. Bailey has been involved with the generation of high-frequency power using solid-state devices. He performed a major portion of the design and development of an all-transistor, 1 kW CW, 400 MHz amplifier. He has also been involved in the design of octave-bandwidth high-power UHF transistor amplifiers. At present, he is working on the development of circuitry for the anomalous mode avalanche diode.

Mr. Bailey is a member of Sigma Pi Sigma.

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C. N. Berglund (S'60–M'65) was born in Fort William, Ont., Canada, on July 21, 1938. He received the B.Sc. degree in electrical engineering from Queen's University, Kingston, Ont., in 1960, the M.S.E.E. degree from the Massachusetts Institute of Technology, Cambridge, in 1961, and the Ph.D. degree in electrical engineering from Stanford University, Stanford, Calif., in 1964.

He was a Research Assistant at M.I.T. during 1960 and 1961, and a Research Associate in the Department of Electrical Engineering at Queen's University, Kingston, from 1961 to 1962. From 1962 to 1964 he was a Research Assistant at the Stanford Electronics Laboratories. Since 1964 he has been a member of the technical staff at Bell Telephone Laboratories, Murray Hill, N. J. He is currently a supervisor in the Semiconductor Device Physics Department.

Dr. Berglund is a member of the American Physical Society.

Arthur J. Brodersen (S'60 – M'66) was born in Fresno, Calif., on August 31, 1939. He received the B.S., M.S., and Ph.D. degrees in electrical engineering in 1961, 1963, and 1966, respectively, from the University of California, Berkeley.

While in school, he held successive appointments as a Research Assistant and Teaching Fellow at the University of California, Berkeley. In 1966, he joined the faculty of the Department of Electrical Engineering at the University of Florida, Gainesville, where he is currently an Associate Professor. His research interests include integrated electronic circuits, noise in semiconductor devices, and automated design of integrated circuits.

Dr. Brodersen is a member of Tau Beta Pi, Eta Kappa Nu, and Sigma Xi.

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Morris Campi was born in Brooklyn, N. Y., on April 20, 1932. He received the B.S. degree in physics from Brooklyn College, Brooklyn, N. Y., in 1960 and the M.S. degree from the American University, Washington, D. C., in 1966.

Since 1960, he has been with the Harry Diamond Laboratories engaged in microwave research and pulse techniques involving microstrip and stripline circuitry and was active in the fields of modulator and oscillator design. His graduate research in wave propagation led to a study of analogous behavior of quantum mechanical tunneling and electromagnetic propagation in a waveguide. He is currently engaged in solid-state material research.

Mr. Campi is a member of the American Physical Society.

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Marvin M. Cohen was born in Manhattan, N. Y., on April 24, 1940. He received the B.A. degree in physics from Brooklyn College, Brooklyn, N. Y., in 1962, and the M.S. and Ph.D. degrees in physics from the American University, Washington, D. C., in 1965 and 1967, respectively.

He has been with the Harry Diamond Laboratories since 1962 and a Professorial Lecturer at the American University since 1968. His work has been concerned with tunneling and scattering mechanisms in solids. At present he is investigating electronic transport in ceramic materials.

Dr. Cohen is a member of the American Physical Society and the American Association for the Advancement of Science.

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Richard C. Jaeger (S'68 – M'69) was born in New York, N. Y., on September 2, 1944. He received the B.S.E.E. and M.E. degrees in 1966, and the Ph.D. degree in 1969, from the University of Florida, Gainesville.

While pursuing his graduate degrees he was an NDEA Fellow, and he is presently employed by IBM Corporation, Boca Raton, Fla.

Dr. Jaeger is a member of Eta Kappa Nu, Phi Kappa Phi, Sigma Tau, and Tau Beta Pi.

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Choong-Ki Kim was born in Seoul, Korea, on October 1, 1942. He received the B.S. degree in engineering from Seoul National University, Seoul, Korea, in 1965 and the M.S. degree in electrical engineering from Columbia University, New York, N. Y., in 1967. He is presently completing the requirements for the Ph.D. degree in electrical engineering at Columbia University. His research interests are in semiconductor devices.

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Juan R. Maldonado was born in Holguin, Cuba, on May 6, 1938. He received a doctorate in physical and mathematical sciences from the University of Havana, Cuba, in 1961, and the Ph.D. degree in physics from the

University of Maryland, College Park, in 1968.

He worked in electronic circuits design at the Physics Department of the University of Maryland from 1962 to 1964. In 1964 he became a Research Assistant in the Low Temperature Solid State Physics Group of the University of Maryland. He joined Bell Telephone Laboratories, Inc., Murray Hill, N. J., in 1968. He is presently working with ferroelectric ceramic materials for electroopic device applications in the Optical Control Device Department at Murray Hill.

Dr. Maldonado is a member of the American Physical Society, Sigma Xi, and Sigma Pi Sigma.

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Bruce A. McDonald (M'66) was born in Stamford, Conn. on October 1, 1941. He received the B.S. degree from Fairfield University, Fairfield, Conn., in 1963 and the M.S. degree from Fordham University, New York, N. Y., in 1965, both in physics.

In 1965 he joined the microelectronics research and development section at the Norden Division of United Aircraft Corporation, Norwalk, Conn. Since 1967 he has been a member of the Research and Development Laboratory of Fairchild Semiconductor, Palo Alto, Calif., where he is working on bipolar h_{FE} degradation mechanisms.

Mr. McDonald is a member of the American Physical Society.

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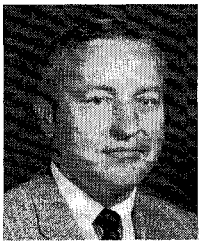

Allen H. Meitzler (M'56) was born in Allentown, Pa., on December 16, 1928. He received the B.S. degree in physics from Muhlenbergh College, Allentown, Pa., in 1951, and the Ph.D. degree in physics from Lehigh University, Bethlehem, Pa., in 1955.

After receiving his graduate degree, he joined Bell Telephone Laboratories, Inc., Whippany, N. J., and worked primarily in the area of research and development problems relating to ultrasonic delay lines. He is presently a supervisor in the Optical Control Device Department at Bell Telephone Laboratories, Murray Hill, N. J., and is working with ferroelectric ceramic and single-crystal materials for electrooptic and acoustooptic device applications.

Dr. Meitzler is a member of the American Physical Society, and a Fellow of the Acoustical Society of America. He was Chairman of the Administrative Committee of the IEEE Group on Sonics and Ultrasonics and is presently the Secretary-Treasurer of that group.

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Richard B. Robrock, II (S'65–M'67) was born in Cleveland, Ohio, on December 29, 1941. He received the B.S. degree in engineering science and the M.S. and Ph.D. degrees in electrical engineering from Case Institute of Technology, Cleveland, Ohio, in 1963, 1965, and 1967, respectively.

During the summers of 1962 and 1963 he was associated with Keithley Instruments, Cleveland, Ohio, and the Motorola Company in Chicago, Ill., respectively. While attending graduate school he published numerous papers in the fields of physiological telemetry and incremental computation. In 1967, he joined Bell Telephone Laboratories, Inc., Holmdel, N. J., where he has worked on bulk semiconductor devices.

Dr. Robrock is a member of Tau Beta Pi, Sigma Xi, and the AAAS.

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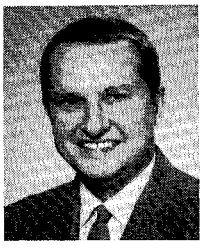

Charles W. Steele (S'47–A'50–M'55) was born in Galesburg, Ill., on November 13, 1924. He received the B.S. and M.S. degrees in electrical engineering from the University of Illinois, Urbana, in 1948 and 1950, respectively. He received another M.S. degree in computer science from Stanford University, Stanford, Calif., in 1967.

He engaged in antenna research and development at Electronics Research, Inc., Evansville, Ind., from 1950 to 1951, and at Stanford Research Institute, Menlo Park, Calif., from 1951 to 1956. From 1956 to 1959 he was concerned with study and development of microwave devices at General Electric Microwave Laboratory, Palo Alto, Calif., and between 1959 and 1963 he supervised the development of antennas and microwave at Philco Western Development Laboratories, Palo Alto, Calif. He was a technical staff member at Stanford Linear Accelerator Center from 1963 to 1964. He joined Ames Research Center, Moffett Field, Calif., as a mathematician in March 1965. In May 1966 he joined Ampex Corporation, Redwood City, Calif., where he is now an applied mathematician and a member of the research staff.

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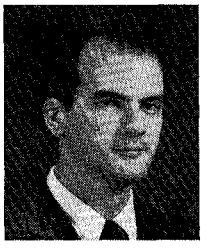

R. H. Walden (S'62 – M'63) was born in New York, N. Y., on May 24, 1939. He received the B.E.S. degree in engineering science in 1962, the M.E.E. degree in electrical engineering in 1963, and the Ph.D. degree in engineering science in 1966, all from New York University, Bronx, N. Y.

He was a research assistant from 1963 to 1965 and a NASA trainee from 1965 to 1966 at New York University. Since 1966 he has been a member of the technical staff at Bell Telephone Laboratories, Murray Hill, N. J.

Dr. Walden is a member of Eta Kappa Nu, Sigma Xi, and the American Physical Society.

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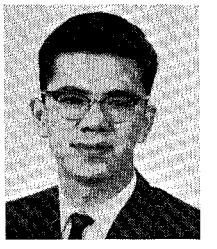

Edward S. Yang (A'61–S'64–M'66) was born in Nanking, China, on October 16, 1936. He received the B.S.E.E. degree from Cheng-Kung University of Tainan, Tainan, Taiwan, the M.S.E.E. degree from Oklahoma State University, Stillwater, Okla., and the Ph.D. degree in engineering and applied science from Yale University, New Haven, Conn., in 1957, 1961, and 1965, respectively.

From 1961 to 1963, he was with the Components Division, IBM Corporation, in Poughkeepsie, N. Y., and from 1963 to 1965, he was a Teaching and Research Assistant at Yale University. Since 1965, he has been an Assistant Professor of Electrical Engineering at Columbia University, New York, N. Y. His research interests are in semiconductor devices and integrated functional devices and circuits.

Dr. Yang is a member of Sigma Xi.

IEEE JOURNAL OF QUANTUM ELECTRONICS, VOL. QE-5, NO. 2, FEBRUARY 1970

IEEE TRANSACTIONS ON MICROWAVE THEORY AND TECHNIQUES, VOL. MTT-18, NO. 2, FEBRUARY 1970

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